

TOSHIBA PHOTOCOUPLER GaAlAs IRED & PHOTO-IC

TLP 251 F

INVERTER FOR AIR CONDITIONOR

INDUCTION HEATING

TRANSISTOR INVERTER

POWER MOS FET GATE DRIVE

IGBT GATE DRIVE

The Toshiba TLP251F consists of a GaAlAs light emitting diode and a integrated photodetector.

This unit is 8-lead DIP package.

TLP251F is suitable for gate driving circuit of IGBT or power MOS FET. Especially TLP251 is capable of “direct” gate drive of lower power IGBTs. (~15A)

- Input Threshold Current : $I_F = 5\text{mA}$ (Max.)
- Supply Current : 11mA (Max.)
- Supply Voltage : $10 \sim 35\text{V}$
- Output Peak Current : $\pm 0.4\text{A}$ (Max.)
- Switching Time : $t_{pHL}, t_{pLH} = 1\mu\text{s}$ (Max.)
- Isolation Voltage : $2500V_{\text{rms}}$ (Min.)
- UL Recognized : UL1577, File No.E67349
- Option (D4) type

VDE Approved : DIN VDE0884 / 06.92, Certificate No.87447

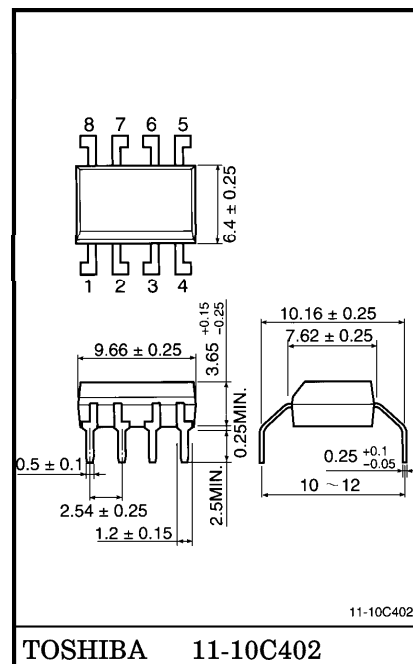
Maximum Operating Insulation Voltage : 1140V_{PK}

Highest Permissible Over Voltage : 6000V_{PK}

(Note 1) When a VDE0884 approved type is needed,
please designate the "Option (D4)"

- Structural Parameter
 - Creepage Distance : 8.0mm (Min.)
 - Clearance : 8.0mm (Min.)

Unit in mm

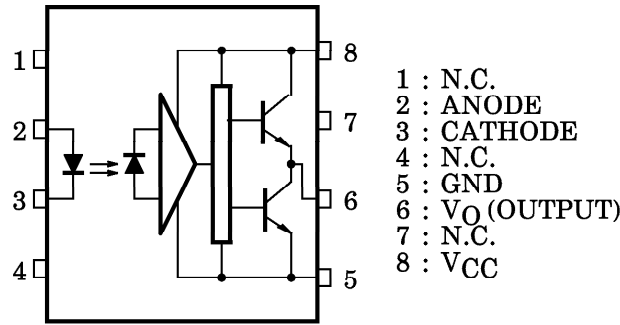


Weight : 0.54g

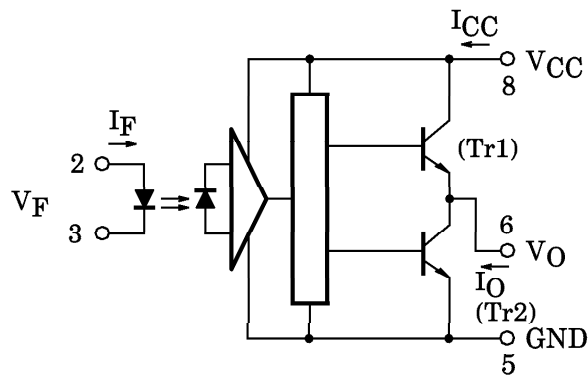
TRUTH TABLE

		Tr1	Tr2
Input LED	ON	ON	OFF
	OFF	OFF	ON

PIN CONFIGURATION (TOP VIEW)



SCHMATIC



(Note 2) A $0.1\mu\text{F}$ bypass capacitor must be connected between pin 8 and 5.

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